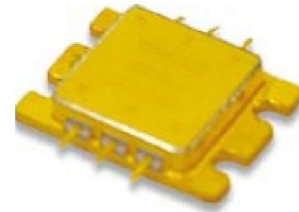


Performance

- Frequency: 3.1-3.5GHz
- Power Gain: 12dB
- Output Power: 56dBm
- PAE: 55%
- Bias Voltage: 48V/-2.3V@3A
- Chip size: 24.0*17.4*4.4mm

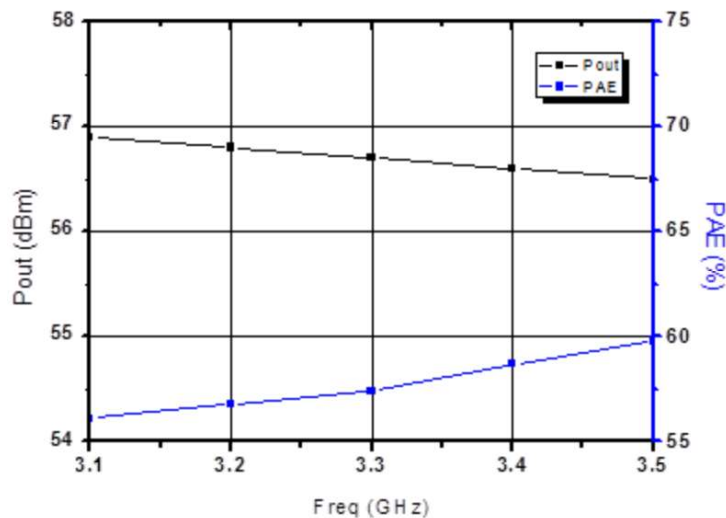


Electrical Specifications (Ta=+25°C, 50Ω system)

Symbol	Parameter	Test Condition	Min	Typical	Max	Unit
G _p	Power Gain	V _d =48V, V _g =-2.3V, I _D ≈3A Freq: 3.1-3.5GHz 100us, 10% D.C	-	12	-	dB
P _{sat}	Saturated Power		-	56	-	dB
PAE	Power Added Efficiency		-	55	-	%
ΔG _p	Gain Flatness		-0.8	-	+0.8	dB

Test Curves

P_{out}, PAE vs. Frequency

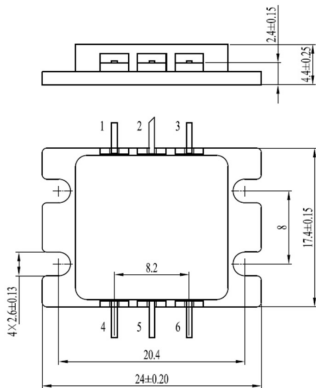


Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	125V	
V _g	Gate Voltage	-10V	
P _d	DC Power	150W	
T _{ch}	Channel Temperature	225°C	
T _m	Mounting Temperature	310°C	1min, N ₂ protection
T _{stg}	Storage Temperature	-55~175°C	

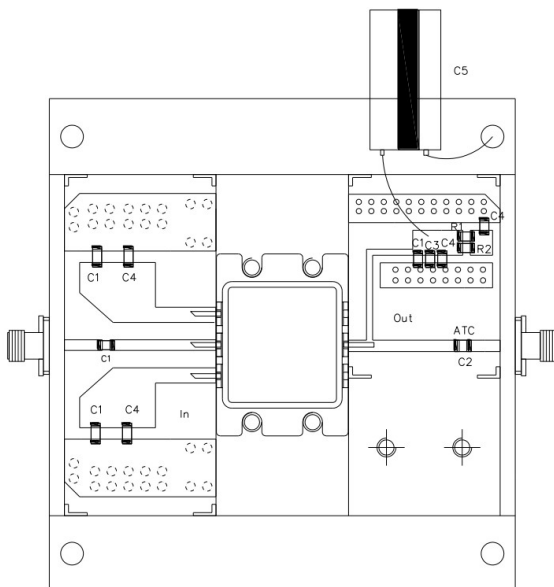
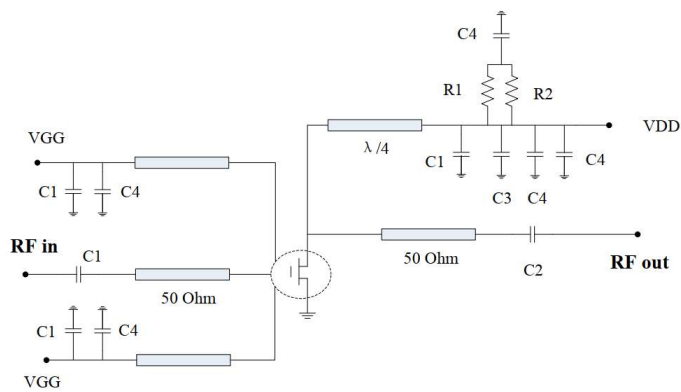
Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Pin Number	Description
1,3	Vgs
4,6	Vds
2	RFin
5	RFout

Application Circuit



Description		Qty
R1	RES,51 OHM,+/-1%,1/16W,0603	1
R2	RES,100 OHM,+/-1%,1/16W,0603	1
C1	CAP,20pF,+/-0.25%,100V,0603	3
C2	ATC CAP,33pF,+/-1%,100V,0805	1
C3	CAP,100pF,+/-5%,100V,0603	1
C4	CAP,1000pF,5%,100V,0603,X	3
C5	CAP,2200µF,100V	1